

2. (amended) A method according to claim 1, wherein the plasma is a high-density plasma having an electron density of $1 \times 10^{10} \text{cm}^{-3}$ or higher.

4. (amended) A method according to claim 1, wherein the step of arranging the sample on a stage includes holding the sample on the stage by electrostatic chucking, the sample being treated by applying the rf bias to the stage independently of the plasma generation and time modulating the rf bias.

6. (amended) A method according to claim 1, wherein the underlying film which underlies the gate electrode film is a gate oxide film.

7. (amended) A method according to claim 1, wherein the gate electrode film is a polysilicon film or a multi-layered film including a polysilicon film.

REMARKS

Applicants reaffirm the provisional election with traverse of the invention of Group I, claims 1-7, in response to the telephone election requirement, and note that claims 8-16 stand withdrawn from consideration.

By the present amendment, the specification has been amended to overcome the objection to the disclosure as noted by the Examiner, with claim 2 being amended in a similar manner. Additionally, claim 1 has been amended to incorporate the features of claim 6 therein, while being amended to clarify features of the present invention, with claims 1, 2, 4, 6 and 7 being amended in a manner which should overcome the rejection of claims 6 and 7 under 35 U.S.C. §112, second paragraph.